

Insulated Gate Bipolar Transistor (Warp 2 Speed IGBT), 100 A



SOT-227

FEATURES

- Ultrafast: Optimized for minimum saturation voltage and speed 0 to 40 kHz in hard switching, > 200 kHz in resonant mode
- Very low conduction and switching losses
- Fully isolated package (2500 V_{AC}/RMS)
- Very low internal inductance (≤ 5 nH typical)
- Industry standard outline
- UL approved file E78996 
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial market


RoHS
COMPLIANT

PRODUCT SUMMARY

V _{CES}	600 V
I _C DC	100 A
V _{CE(on)} at 100 A, 25 °C	1.8 V

BENEFITS

- Designed for increased operating efficiency in power conversion: PFC, UPS, SMPS, welding, induction heating
- Lower overall losses available at frequencies ≥ 20 kHz
- Easy to assemble and parallel
- Direct mounting to heatsink
- Lower EMI, requires less snubbing
- Plug in compatible with other SOT-227 packages

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter breakdown voltage	V _{CES}		600	V
Continuous collector current	I _C	T _C = 25 °C	100	A
		T _C = 100 °C	50	
Pulsed collector current	I _{CM}		200	
Clamped inductive load current	I _{LM}	Repetitive rating: V _{GE} = 20 V; pulse width limited by maximum junction temperature (fig. 20)	200	
Gate to emitter voltage	V _{GE}		± 20	V
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	
Maximum power dissipation	P _D	T _C = 25 °C	250	W
		T _C = 100 °C	100	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C
Mounting torque		6 to 32 or M3 screw	12 (1.3)	lbf · in (N · m)

THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TYP.	MAX.	UNITS
Junction to case, IGBT	R _{thJC}	-	0.50	°C/W
Thermal resistance, junction to case, diode	R _{thJC}	-	1.0	
Case to sink, flat, greased surface	R _{thCS}	0.05	-	
Weight of module		30	-	g

**ELECTRICAL SPECIFICATIONS** ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{ V}$, $I_C = 250\text{ }\mu\text{A}$ $V_{GE} = 0\text{ V}$, $I_C = 1.0\text{ mA}$	600	-	-	V
Temperature coefficient of breakdown voltage	$\Delta V_{(BR)CES}/\Delta T_J$		-	0.36	-	V/ $^{\circ}\text{C}$
Collector to emitter saturation voltage	$V_{CE(on)}$	$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$	-	1.49	2.1	V
		$V_{GE} = 15\text{ V}$, $I_C = 100\text{ A}$	-	1.80	-	
		$V_{GE} = 15\text{ V}$, $I_C = 50\text{ A}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	1.47	-	
Gate threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	3.0	-	6.0	
Temperature coefficient of threshold voltage	$\Delta V_{GE(th)}/\Delta T_J$	$V_{CE} = V_{GE}$, $I_C = 250\text{ }\mu\text{A}$	-	- 7.6	-	mV/ $^{\circ}\text{C}$
Forward transconductance	g_{fe}	$V_{CE} = 100\text{ V}$, $I_C = 50\text{ A}$	34	52	-	S
Zero gate voltage collector current	I_{CES}	$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$	-	-	250	μA
		$V_{GE} = 0\text{ V}$, $V_{CE} = 600\text{ V}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	-	1.3	mA
Diode forward voltage drop	V_{FM}	$I_C = 50\text{ A}$	-	1.3	1.6	V
		$I_C = 50\text{ A}$, $T_J = 150\text{ }^{\circ}\text{C}$	-	1.16	1.3	
Gate to emitter leakage current	I_{GES}	$V_{GE} = \pm 20\text{ V}$	-	-	± 100	nA

SWITCHING CHARACTERISTICS ($T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Total gate charge (turn-on)	Q_g	$I_C = 50\text{ A}$ $V_{CC} = 400\text{ V}$ $V_{GE} = 15\text{ V}$	-	430	640	nC
Gate emitter charge (turn-on)	Q_{ge}		-	48	72	
Gate collector charge (turn-on)	Q_{gc}		-	130	190	
Turn-on delay time	$t_{d(on)}$	$T_J = 25\text{ }^{\circ}\text{C}$ $I_C = 60\text{ A}$, $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$, $R_g = 5.0\text{ }\Omega$ energy losses include "tail" and diode reverse recovery	-	57	-	ns
Rise time	t_r		-	80	-	
Turn-off delay time	$t_{d(off)}$		-	240	-	
Fall time	t_f		-	120	-	
Turn-on switching loss	E_{on}		-	0.41	-	mJ
Turn-off switching loss	E_{off}		-	2.51	-	
Total switching loss	E_{ts}		-	2.92	4.4	
Turn-on delay time	$t_{d(on)}$	$T_J = 150\text{ }^{\circ}\text{C}$ $I_C = 60\text{ A}$, $V_{CC} = 480\text{ V}$ $V_{GE} = 15\text{ V}$, $R_g = 5.0\text{ }\Omega$ energy losses include "tail" and diode reverse recovery	-	57	-	ns
Rise time	t_r		-	80	-	
Turn-off delay time	$t_{d(off)}$		-	380	-	
Fall time	t_f		-	170	-	
Total switching loss	E_{ts}		-	4.78	-	mJ
Internal emitter inductance	L_E		-	2.0	-	nH
Input capacitance	C_{ies}	$V_{GE} = 0\text{ V}$ $V_{CC} = 30\text{ V}$ $f = 1.0\text{ MHz}$	-	7400	-	pF
Output capacitance	C_{oes}		-	730	-	
Reverse transfer capacitance	C_{res}		-	90	-	
Diode reverse recovery time	t_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$	-	90	140	ns
		$T_J = 125\text{ }^{\circ}\text{C}$	-	120	180	
Diode peak reverse recovery current	I_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$	-	7.3	11	A
		$T_J = 125\text{ }^{\circ}\text{C}$	-	11	16	
Diode reverse recovery charge	Q_{rr}	$T_J = 25\text{ }^{\circ}\text{C}$	-	360	550	nC
		$T_J = 125\text{ }^{\circ}\text{C}$	-	780	1200	
Diode peak rate of fall recovery during t_b	$dl_{(rec)M}/dt$	$T_J = 25\text{ }^{\circ}\text{C}$	-	370	-	A/ μs
		$T_J = 125\text{ }^{\circ}\text{C}$	-	220	-	

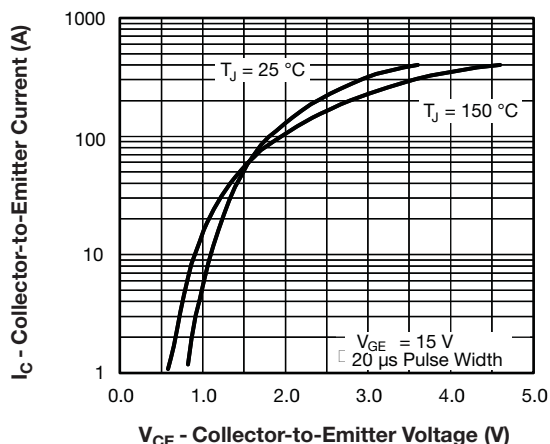


Fig. 1 - Typical Output Characteristics

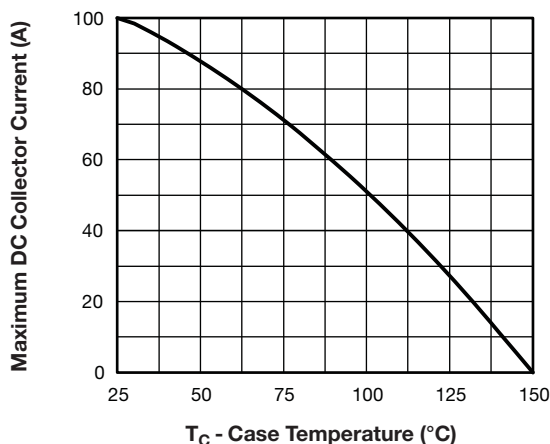


Fig. 3 - Maximum Collector Current vs. Case Temperature

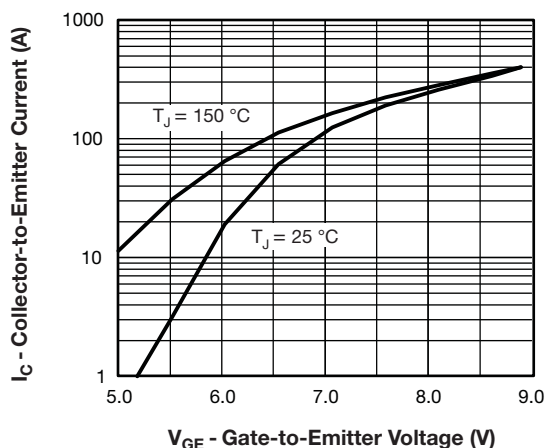


Fig. 2 - Typical Transfer Characteristics

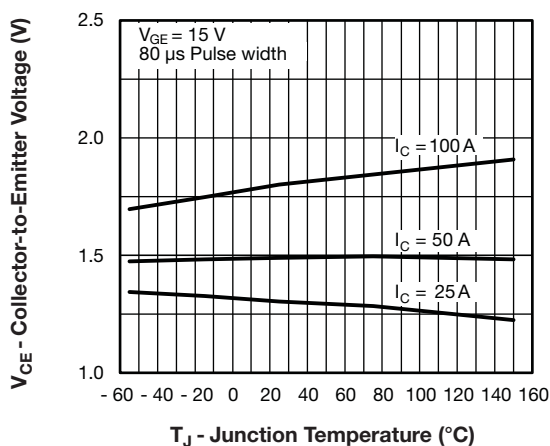


Fig. 4 - Typical Collector to Emitter Voltage vs. Junction Temperature

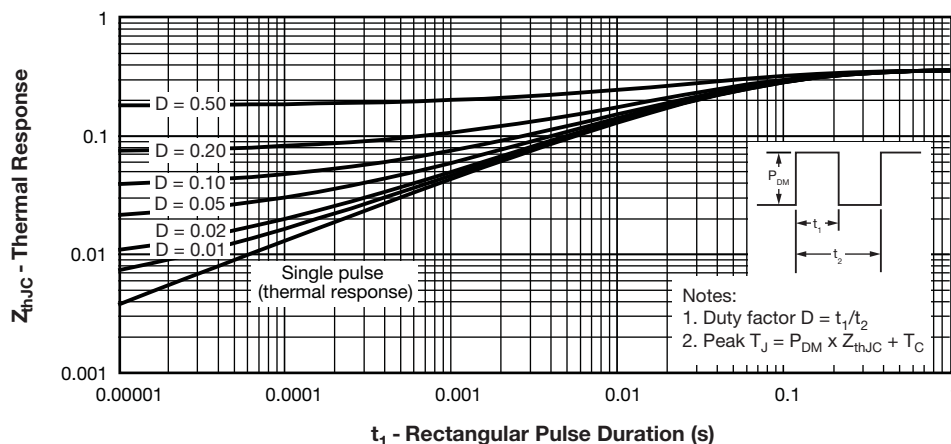


Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction to Case

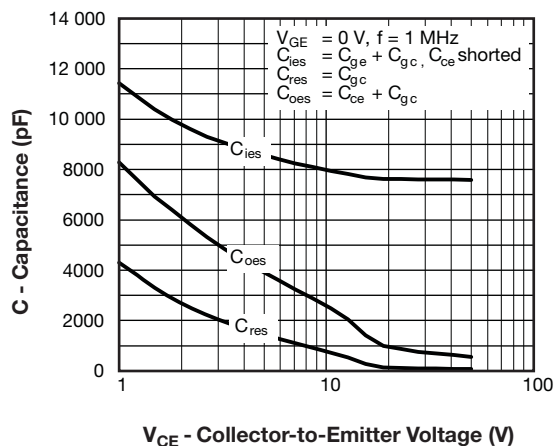


Fig. 6 - Typical Capacitance vs. Collector to Emitter Voltage

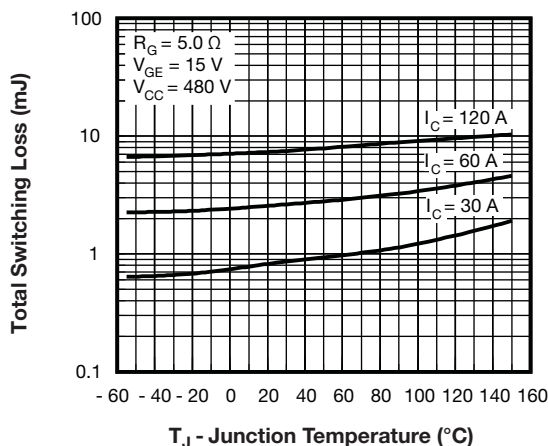


Fig. 9 - Typical Switching Losses vs. Junction Temperature

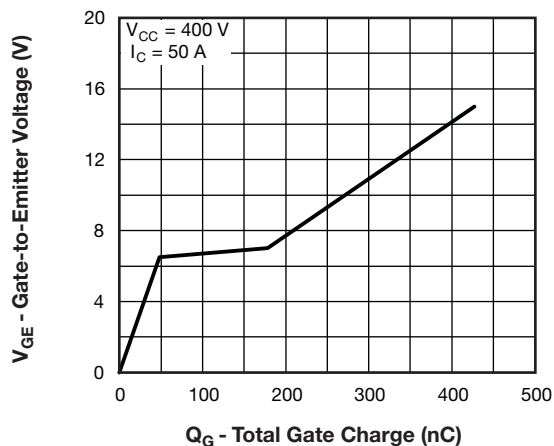


Fig. 7 - Typical Gate Charge vs. Gate to Emitter Voltage

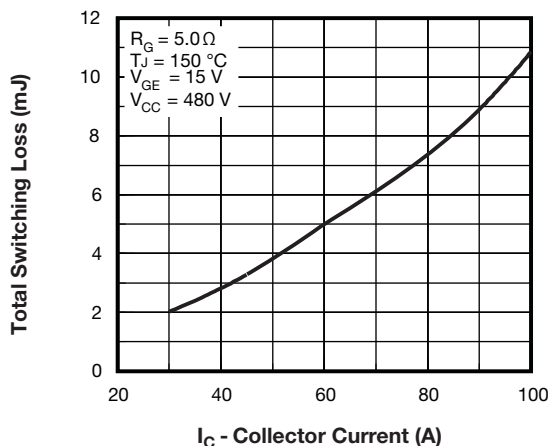


Fig. 10 - Typical Switching Losses vs. Collector to Emitter Current

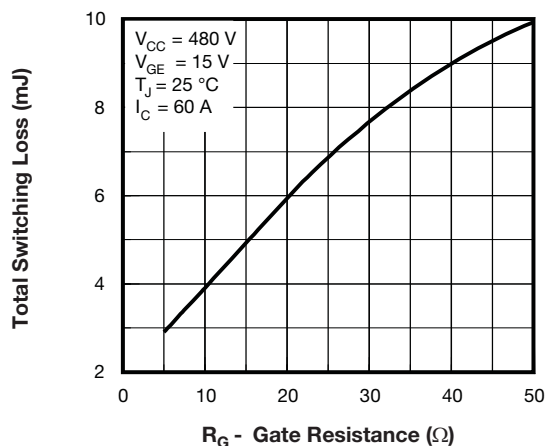


Fig. 8 - Typical Switching Losses vs. Gate Resistance

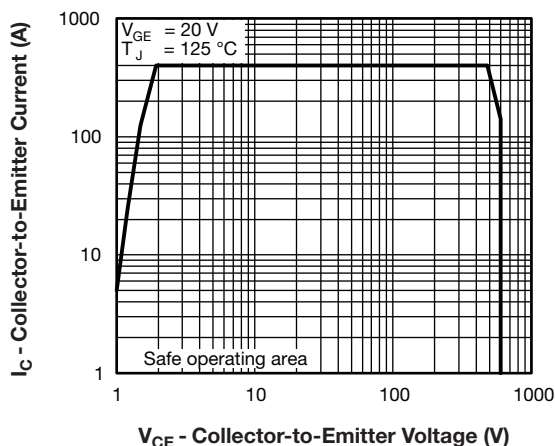


Fig. 11 - Turn-Off SOA

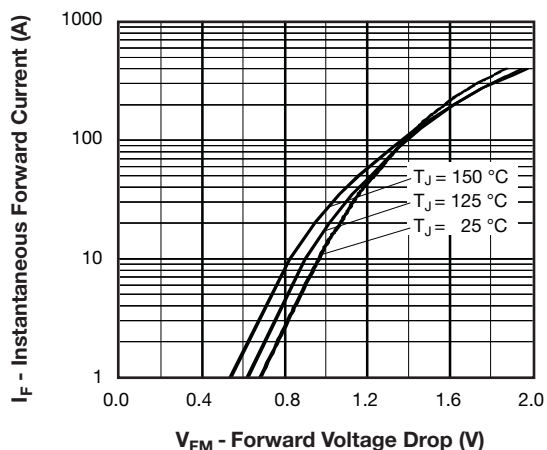


Fig. 12 - Typical Forward Voltage Drop vs. Instantaneous Forward Current

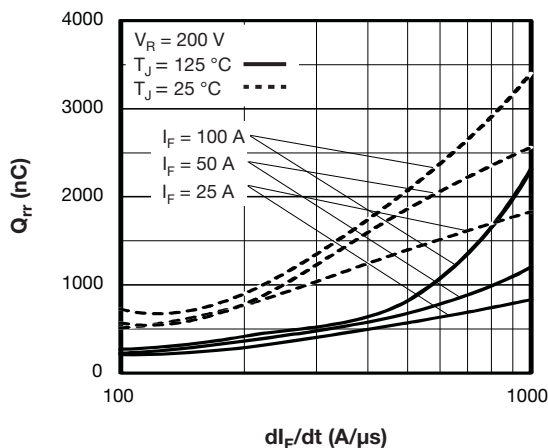


Fig. 15 - Typical Stored Charge vs. dI_F/dt

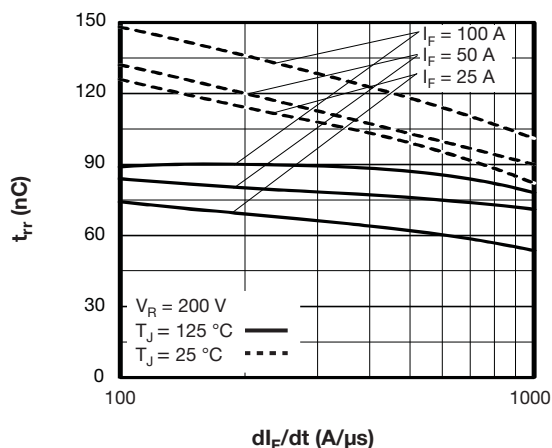


Fig. 13 - Typical Reverse Recovery vs. dI_F/dt

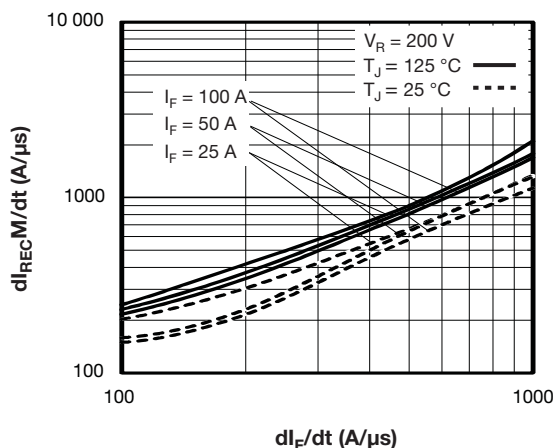


Fig. 16 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

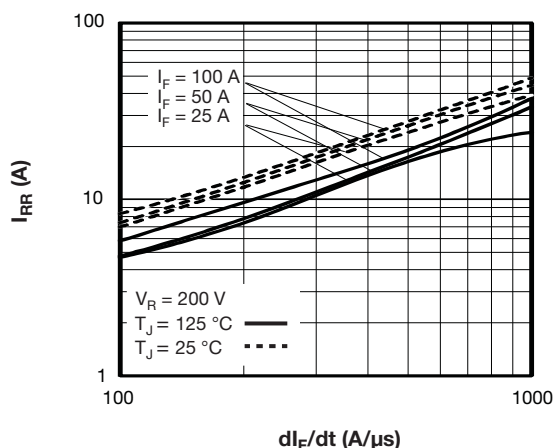


Fig. 14 - Typical Recovery Current vs. dI_F/dt

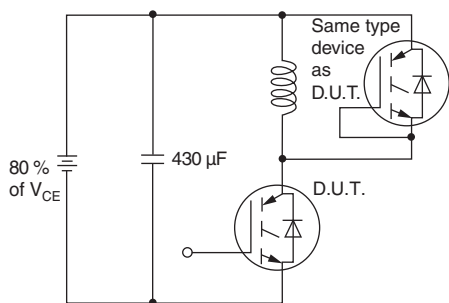


Fig. 17a - Test Circuit for Measurement of I_{LM} , E_{on} , $E_{off}(\text{diode})$, t_{rr} , Q_{rr} , I_{rr} , $t_{d(on)}$, t_r , $t_{d(off)}$, t_f

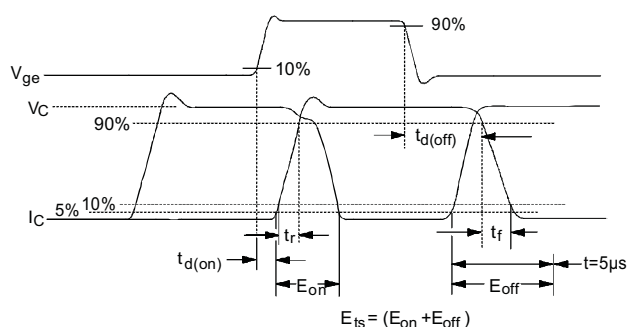


Fig. 17b - Test Waveforms for Circuit of Fig. 17a, Defining E_{off} , $t_{d(off)}$, t_f

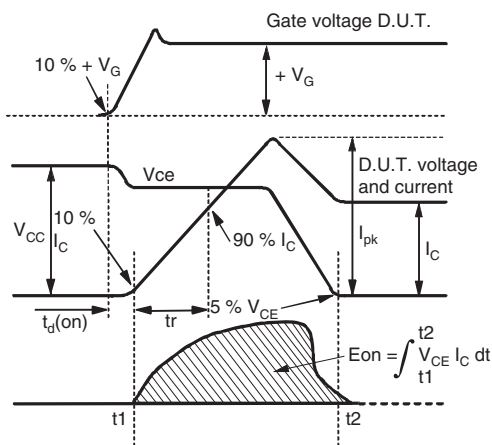


Fig. 17c - Test Waveforms for Circuit of Fig. 17a, Defining E_{on} , $t_{d(on)}$, t_r

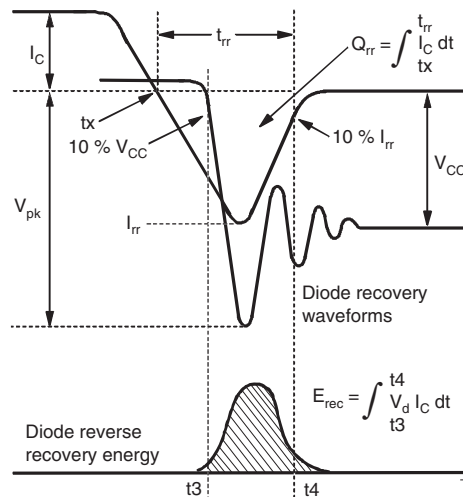


Fig. 1 - Test Waveforms for Circuit of Fig. 17a, Defining E_{rec} , t_{rr} , Q_{rr} , I_{rr}

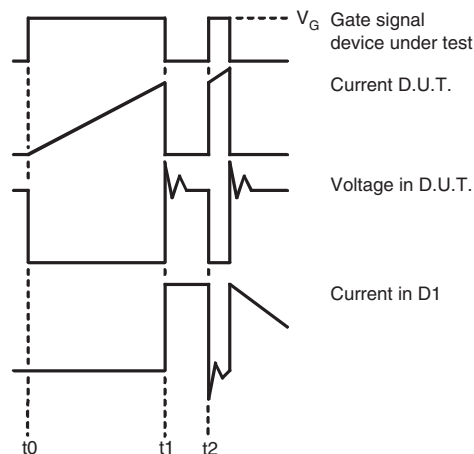


Fig. 17e - Macro Waveforms for Figure 17a's Test Circuit

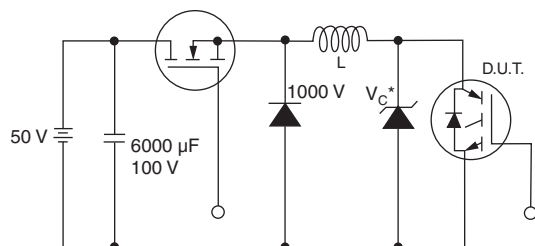


Fig. 18a - Clamped Inductive Load Test Circuit

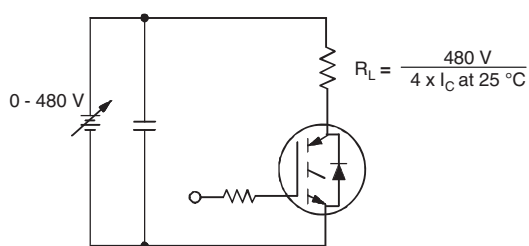
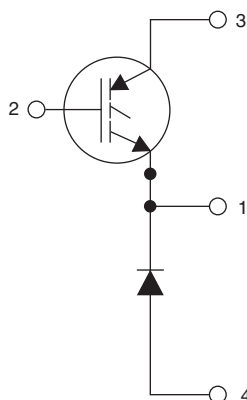


Fig. 18b - Pulsed Collector Current Test Circuit

ORDERING INFORMATION TABLE

Device code	VS-	G	A	100	N	A	60	U	P
	1	2	3	4	5	6	7	8	9
1	Vishay Semiconductors product								
2	Device:								
	G = IGBT								
3	Silicon technology:								
	A = Generation 4 IGBT, Generation 2 HEXFRED®								
4	Current rating (100 = 100 A)								
5	N = High side chopper								
6	SOT-227								
7	Voltage rating (60 = 600 V)								
8	U = Ultrafast with matching diode								
9	- None = Standard production - P = Lead (Pb)-free								

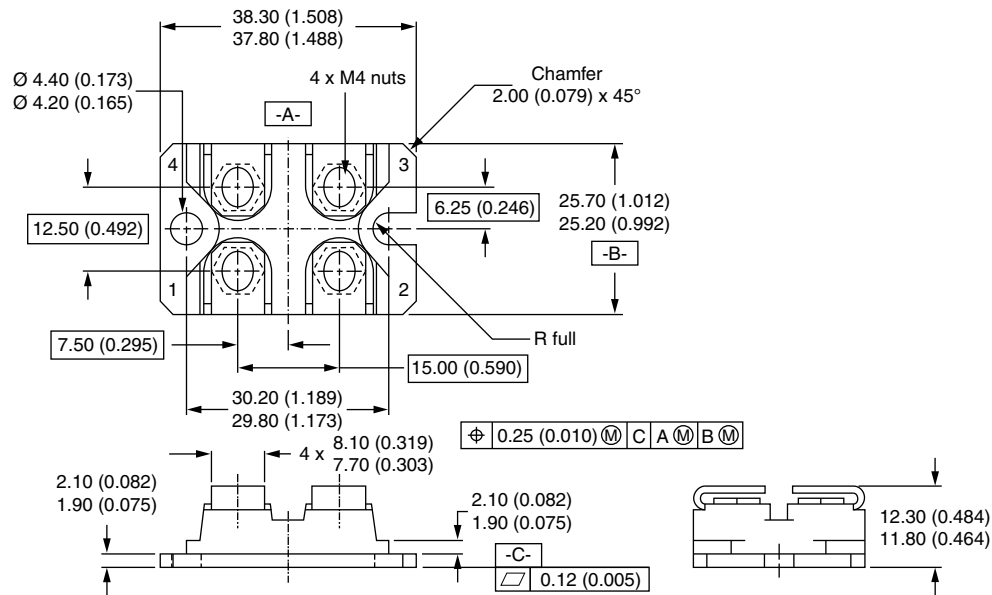
CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95036
Packaging information	www.vishay.com/doc?95037

SOT-227

DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



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